



Title of Change:	Wafer fab transfer from ADVANCED MICROELECTRONIC PRODUCTS, INC. (AMPI) in Taiwan to ON Semiconductor Niigata in Japan.
Proposed first ship date:	15 November 2017 or earlier upon customer approval
Contact information:	Contact your local ON Semiconductor Sales Office or <Tomohiro.Uda@onsemi.com>
Samples:	Contact your local ON Semiconductor Sales Office
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or <Kazutoshi.Kitazume@onsemi.com>
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <PCN.Support@onsemi.com>.
Change Part Identification:	Affected products will be identified with lot code.
Change category:	<input checked="" type="checkbox"/> Wafer Fab Change <input type="checkbox"/> Assembly Change <input type="checkbox"/> Test Change <input type="checkbox"/> Other _____
Change Sub-Category(s):	<input checked="" type="checkbox"/> Manufacturing Site Change/Addition <input type="checkbox"/> Material Change <input type="checkbox"/> Datasheet/Product Doc change <input type="checkbox"/> Manufacturing Process Change <input type="checkbox"/> Product specific change <input type="checkbox"/> Shipping/Packaging/Marking <input type="checkbox"/> Other: _____
Sites Affected:	<input type="checkbox"/> All site(s) <input type="checkbox"/> not applicable <input checked="" type="checkbox"/> ON Semiconductor site(s) : ON Niigata, Japan <input type="checkbox"/> External Foundry/Subcon site(s) ADVANCED MICROELECTRONIC PRODUCTS, INC.
Description and Purpose:	<p>This Final Process Change Notification is to announce the fab transfer of MOSFET in IPM from ADVANCED MICROELECTRONIC PRODUCTS, INC (AMPI) in Taiwan to ON Semiconductor Niigata in Japan.</p> <p>The MOSFET design and electrical specifications will remain identical.</p>



Reliability Data Summary:

QV DEVICE NAME: STK672-640AN-E

RMS: J41057

PACKAGE: SIP-S

Test	Specification	Condition	Interval	Results
H3TRB	EIAJ ED-4701/100 Test Method 102	Ta=85°C, 85%RH, Vcc=80V, Vdd=6V	1000hrs	0/11
AC	EIAJ ED-4701 B-123	Ta=121°C,100%RH, 2.05x10 ⁵ Pa	96hrs	0/11
TC	EIAJ ED-4701/100 Test Method 105	Ta= -40°C to +125°C	1000cyc	0/11
HTSL	EIAJ ED-4701/200 Test Method 201	Ta = 125°C	1000hrs	0/11
HTRB	EIAJ ED-4701/100 Test Method 101	Ta = 125°C, Vcc=80V, Vdd=6V	1000hrs	0/11
ESD (MM)	EIAJ ED-4701/300 C-111	C=200pF, R=0Ω, V=±200V	1time	0/3
ESD (HBM)	EIAJ ED-4701/300 Test Method 304	C=100pF, R=1500Ω, V=±2000V	3times	0/3

This reliability test data is the model that is the highest power supply condition in the voltage in all models.

Electrical Characteristic Summary:

There is no change in the electrical performance. Datasheet specifications remain unchanged.

List of affected Standard Parts:

Part Number	Qualification Vehicle
STK672-440AN-E	STK672-640AN-E
STK672-442AN-E	
STK672-440BN-E	
STK672-442BN-E	
STK672-640AN-E	
STK672-642AN-E	
STK672-640CN-E	
STK672-740AN-E	
STK672-430AN-E	
STK672-432AN-E	
STK672-432BN-E	
STK672-630AN-E	
STK672-632AN-E	
STK672-630CN-E	
STK672-732AN-E	